Welcome

to today's episode:

CYBERTECHNOLOGIES CT300: THE SWISS ARMY KNIFE (SAK) OF OPTICAL METROLOGY

Karl-Heinz Strass

Managing Director, cyberTECHNOLOGIES USA

March 26, 2024 at 11 AM PT





COVALENT ACADEMY

Industrial Applications of Advanced Metrology Episode 36



Modern, digitally-empowered analytical services platform delivering quality data and expert analysis to accelerate advanced materials and device innovation.



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Particle Analysis: DLS / ELS /

size distribution / zeta potential

Tensile testing

• S/TEM

Diffraction; SAED

• Dye & Pry Test

NIR / IR Imaging

Root-Cause Failure Analysis

Covalent Partners & cyberTECHNOLOGIES





- Develop Optical Metrology Platforms with a modular architecture from the ground up:
 - Integrates a wide range of important measurements in a single package
 - Tools can be customized to clients' specific needs: up to 5 distinct sensors per machine
- cyberTECHNOLOGIES' non-contact 3D measurement systems are widely used in microelectronics and other precision industries – we'll see examples of these applications in the talk today!



Introducing today's speaker...



Karl-Heinz Strass

Managing Director for the Americas, cyberTECHNOLOGIES

- Over 35 years of experience in thin film and surface metrology
 - Specialized in researching and developing metrology systems and applications
- Master's degree in Engineering from the University of Applied Sciences in Munich
- Joined Tencor Instruments (later KLA-Tencor) as an applications engineer
- Worked in various Sales and Marketing roles; now overseeing cyberTECHNOLOGIES' sales and marketing operations across the Americas





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Application Examples

- Monitoring Process Uniformities
- Coplanarity
- Sample Wafer Inspection
- Bump Defect Inspection
- Thickness Measurements

Wrap-Up & Thank You

- Wafer Mapping
- Flatness
- Wafer and Tape Thickness
- Stress Measurement

MEASUREMENT TECHNOLOGIES





MEASUREMENT TECHNOLOGIES





MEASUREMENT TECHNOLOGIES





Sensor Technologies & Use Cases Topography Measurements





Sensor Technologies & Use Cases Film Thickness Measurements



Sensor Technologies	Approx. z Resolution	Typical Use Cases	Examples	
CONFOCAL WHITE LIGHT	P/L-CHR point sensor 70 nm ~ μm	General surface topography, roughness, step heights, BGA, flatnes	S Dispensed dots BGA, Micro-BGA, Solder Deposits	Printed Materials
REFLECTOMETER (Thin Film Thickness)	RFM point sensor 70 nm ~ 5 µm	Thin Film Thickness measurements (<5 um), measurements through transparent films, very high precision		
3D CONFOCAL MICROSCOPE	CFM 2D/3D sensor 1 nm ~ 3 nm	High resolution topography measurements, ie. patterned wafers, etched micro-channels	Metal surface 230µm x 300µm	Opto-electronic device 40µm x 50µm
INTERFEROMETER (Film Thickness)	INT point sensor µm	Film Thickness measurements, measurements through transparent films, conformal coating	Conformal Coating	
INFRA-RED SPECTROMETER	IR-INT point sensor μm	Thickness measurements of Si (transparent for IR), air gap measurements under Si layers	Wafer Thickness Via Depth	11

Sensor Technologies & Use Cases Visual / Defect Inspection





Bio-med sensor

Currency

The Swiss Army Knife of Metrology Automatically switch amongst sensors





The Swiss Army Knife of Metrology Automatically switch amongst sensors





The Swiss Army Knife of Metrology Automatically switch amongst sensors





SYSTEM PLATFORMS





Use Cases for Chromatic Confocal Sensors





Confocal White Light Sensor





- Analysis: Relative Measurement within the sensor range
 - No physical movement of objective within the measurement range

Line Sensor– Point Pitch & Line Width





MODEL	POINT P	псн	LINE WIDT	Н	Numeric Aperture
L-CHR-200	5 µm	0.20 mils	0.96 mm	0.04 inch	0.7
L-CHR-500	7.5 μm	0.30 mils	1.43 mm	0.06 inch	0.61
L-CHR-1000	10 µm	0.39 mils	1.91 mm	0.08 inch	0.55
L-CHR-4000	25 µm	0.98 mils	4.78 mm	0.19 inch	0.33

Line Sensor– Point Pitch Interlaced Step Size Overview



Point Pitch: 7.5 um. interlaced (in this example 3 times for visual simplicity)



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- Stress Measurement

Monitoring Process Uniformities Via sample: multiple profiles overlaid



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Monitoring Process Uniformities "Heat Map"





- Graphical display of feature height, depth, diameter, volume or roughness by location
- Nominal vs actual
- Dot size can represent any measured parameter, like
 - ball height, ~diameter, local roughness, feature height, volume etc.

Coplanarity



- Automatic Analysis
- Seating Plane
- Regression Plane



Bump Height

Bump Radius



Missing Bumps

Coplanarity





Sample Wafer

Program []	ųΧ	Cursor Sets of	Position Ball															
	^	Name	Position		Status			3D Height Maximum		Diameter (Areal-Equivalent)		Coplanarity (Regression Plane)		Center X		Center Y		Positive Plana Area
±-1 (10		Set No.1	Ball	Image: A start of the start	good		V 6	65.03 µm		83.51 µm	-	88.63 µm	 Image: A set of the set of the	97,781.96 µm	~	214,862.77 µm	1	0.00557 mm ²
() ()		Set No.2	Ball		good		V 6	55.13 µm	-	88.62 µm	\checkmark	88.55 µm	 Image: A set of the set of the	97,480.44 µm	\checkmark	214,861.56 µm	1	0.00664 mm ²
		Set No.3	Ball	Image: A start and a start	good	3	V 6	5.16 µm		82.18 µm	1	88.56 µm	1	97,332.89 µm	\checkmark	214,863.13 µm	1	0.00585 mm ²
0-1 Jan		Set No.4	Ball	 Image: A start of the start of	good		🖌 e	54.81 µm	-	86.43 µm	1	89.00 µm	-	96,576.02 µm	1	214,862.65 µm	1	0.00579 mm ²
		Set No.5	Ball	~	good		V 6	5.35 µm	-	85.36 µm	\checkmark	88.42 µm	~	96,273.85 µm	\checkmark	214,862.22 µm	1	0.00568 mm ²
Object Height Z: 10.000.00 um		Set No.6	Ball	-	good		V 6	5.41 µm		85.47 µm	1	88.40 µm	1	96,121.86 µm	1	214,860.90 µm	1	0.00574 mm ²
T Oriser Faler 1 / [11-E C-0]		Set No.7	Ball	Image: A start of the start	good		V 6	5.89 µm		85.96 µm	\checkmark	87.93 µm	~	95,973.57 µm	\checkmark	214,863.46 µm	~	0.00579 mm ²
Offset Layer 1 / [H=2 C=9]		Set No.8	Ball		good		V 6	5.68 µm	-	86.66 µm	\checkmark	88.15 µm	1	95,822.08 µm	1	214,862.69 µm	1	0.00596 mm ²
Cfiset Layer 17 [R=2 C=10]		Set No.9	Ball		good		V 6	5.94 µm		86.26 µm	\checkmark	87.82 µm	- V	95,669.63 µm	\checkmark	214,859.79 µm	1	0.00607 mm ²
Giffeet Layer 17 [R=2 C=11]		Set No.10	Ball	Image: A start of the start	good		V 6	5.38 µm	-	86.59 µm	~	88.31 µm	~	95,519.20 µm	1	214,864.36 µm	1	0.00585 mm ²
Offset Layer 17 [R=2 C=12]		Set No.11	Ball	1	good		V 6	5.85 µm	-	78.33 µm	\checkmark	87.84 µm	1	95,217.02 µm	1	214,861.13 µm	1	0.00495 mm ²
Offset Laver 1 7 [R=2 C=14]		Set No.12	Ball		good		V 6	65.75 µm		80.82 µm	1	87.92 µm	1	95,066.48 µm	1	214,862.63 µm	1	0.00529 mm ²
Offset Laver 17 [R=2 C=15]		Set No.13	Ball	 Image: A second s	good		V 6	6.17 µm	-	85.16 µm	\checkmark	87.45 µm	1	94,918.76 µm	\checkmark	214,861.48 µm	~	0.00562 mm ²
0ffset Laver 1 7 [R=2 C=16]		Set No.14	Ball	 Image: A start of the start of	good		V 6	5.30 µm	-	81.38 µm	1	88.30 µm	1	94,762.76 µm	1	214,862.88 µm	1	0.00506 mm ²
Offset Laver 1 7 [R=2 C=17]		Set No.15	Ball	Image: A start of the start	good		V 6	5.79 µm		80.24 µm	\checkmark	87.79 µm	1	94,616.37 µm	1	214,863.30 µm	1	0.00512 mm ²
H		Set No.16	Ball		good		V 6	5.88 µm	-	84.99 µm	~	87.73 µm	-	94,463.46 µm	1	214,862.34 µm	1	0.00574 mm ²
0ffset Layer 1 7 [R=2 C=19]		Set No.17	Ball	-	good		V 6	6.20 µm	-	82.77 µm	1	87.39 µm	1	94,312.76 µm	1	214,862.61 µm	1	0.00562 mm ²
Define Layer 1 7 [R=2 C=20]		Set No.18	Ball		good		V 6	5.17 µm	-	85.56 µm	\checkmark	88.43 µm	1	94,163.95 µm	1	214,862.45 µm	1	0.00562 mm ²
Image: Offset Layer 1 7 [R=2 C=21]		Set No.19	Ball		good		V 6	6.00 µm	-	85.35 µm	~	87.59 µm	1	94.012.69 µm	1	214,861.17 µm	1	0.00619 mm ²
Offset Layer 1 7 [R=2 C=22]		Set No.20	Ball	-	good		V 6	6.11 µm	-	84.03 µm	1	87.50 µm	1	93,862.15 µm	1	214,860.92 µm	1	0.00551 mm ²
	~	Set No.21	Ball	V	good		V 6	6.27 µm		80.78 µm	1	87.37 µm	1	93,709.01 µm	1	214,862.26 µm	V	0.00551 mm ²
E-moniton Program E-malarar		Set No.22	Ball	1	good		V 6	6.26 µm	-	80.26 µm	V	87.39 µm	1	93,559.72 µm	1	214,861.79 µm	1	0.00523 mm ²
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Simple Program Setup





Wafer Die Grid





Sample Wafer





Full Wafer Bump Height Distribution





Sample Wafer – Wafer May by Die





Sample Wafer – Height



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Height – equal Numbers



Sample Wafer – Height vs Diameter vs Volume Distribution







Fully automated analysis of x/y deviation across the entire sample



Each individual feature or other specified measurement location is automatically analyzed for nominal vs actual position

Bump Defect Inspection: Bump Height Uniformity across sample









0.5 μm x 0.5 μm Step, LCHR-200





0.5 μm x 0.5 μm Step, 1.00 -LCHR-200

0.5 μm x 0.5 μm Step, LCHR-200

Thickness– Thinned Silicon Wafer Dual-sided CTx50T Systems

- Fast and accurate thickness measurement over large areas
- Total Thickness, Total Thickness Variation, Warpage, Bow, Stress

0.27550 mm 0.27450 mm 0.27350 mm 0.27250 mm 0.27150 mm 0.27050 mm 0.26950 mm 0.26850 mm 0.26750 mm 0.26650 mm 0.26550 mm 0.26450 mm 0.26350 mm 0.26250 mm 0.26150 mm

Wafer Mapping

Flatness

Warpage

Thickness

Blank or patterned wafers

- Flatness across entire sample up to 1 m x 2 m (> 3' x 6')
- Macro & Micro Measurement
 - Full Wafer & w/in Stepper Exp Field
- Detection of Bow and Warpage
- Gravity Compensation
- Stress Measurement
- Film Thickness Variation

Flatness

- Flatness across entire sample up to 1 m x 2 m (> 3' x 6')
- Macro & Micro Measurement
 - Full Wafer & w/in Stepper Exp Field
- Detection of Bow and Warpage
- Gravity Compensation
- Stress Measurement
- Film Thickness Variation

Wafer & Tape Thickness

Wafer & Tape Thickness

Thickness Measurement	Avg Thk [um]	StdDev of Thk [um]	Stdev [%]	Thickness Massurement A, B, C
A+B+C				
[R=1 C=3]	758.1	0.833	0.11%	758.5 0.900
[R=2 C=2]	757.8	0.860	0.11%	758.0 0.880
[R=2 C=3]	757.8	0.874	0.12%	757.5
[R=2 C=4]	755.3	0.864	0.11%	757.0 0.840
[R=3 C=1]	756.5	0.824	0.11%	756.5
[R=3 C=2]	756.0	0.788	0.10%	756.0
[R=3 C=3]	757.6	0.886	0.12%	755.5
[R=3 C=4]	757.4	0.804	0.11%	755.0
[R=3 C=5]	755.7	0.796	0.11%	754.5
[R=4 C=2]	757.3	0.854	0.11%	754.0 0.740
[R=4 C=3]	757.6	0.793	0.10%	
[R=4 C=4]	757.4	0.804	0.11%	
[R=5 C=3]	756.5	0.792	0.10%	Avg Thk [um] StdDev of Thk [um]
Wafer Thickness [1]	Avg Thk [um]	StdDev of Thk [um]	Stdev [%]	Wafar Thicknos
[R=1 C=3]	635.3	0.942	0.15%	vvaret filickries
[R=2 C=2]	633.7	0.865	0.14%	636.0 1.000
[R=2 C=3]	634.0	0.884	0.14%	635.0
[R=2 C=4]	631.9	0.871	0.14%	
[R=3 C=1]	632.2	0.835	0.13%	634.0 0.900
[R=3 C=2]	632.2	0.794	0.13%	633.0 0.850
[R=3 C=3]	633.8	0.881	0.14%	
[R=3 C=4]	633.8	0.808	0.13%	632.0 0.800
[R=3 C=5]	632.2	0.795	0.13%	631.0 0.750
[R=4 C=2]	633.3	0.850	0.13%	630.0 0.700
[R=4 C=3]	633.7	0.801	0.13%	1 2 3 4 5 6 7 8 9 10 11 12 13
[R=4 C=4]	633.7	0.808	0.13%	Avg Thk [um] StdDev of Thk [um]
[R=5 C=3]	632.7	0.795	0.13%	

Wafer & Tape Thickness

P) DTTOM	Test Wafer and Tape Thicknes	Name	Status	3D Height Avg	Center X	Center Y	Ra - Average Roughness	Rt - Peak to Valley Height (Roughness)	Wafer Thickness
E B	Scan No. 1 [R=2 C=2]	Scan No. 10 [R=4 C=2] 🗸	good	🗸 Ø 336.677 µm	Ø 155,778.900 µm 🖌	Ø 200,465.200 µm 🖌	Ø 0.004 µm 🖌	Ø 0.030 µm 🗹	Ø 424.209 µm
8 8 8		Scan No. 10 [R=4 C=3] 🗸	good	🗹 Ø 336.807 µm 🗧	Ø 163,778.900 µm 🗸	Ø 200,465.200 µm 🗸	Ø 0.002 µm 🖌	Ø 0.022 µm 🖌	Ø 424.133 µm
V 50		Scan No. 10 [R=4 C=4] 🗸	good	🗸 Ø 351.918 µm 🖌	🖌 Ø 171,778.900 µm 🖌	Ø 200,465.200 µm 🗸	Ø 0.006 µm 🗸	Ø 0.045 µm 🖌	Ø 393.800 µm
RV elle		Scan No. 10 [R=5 C=3] 🗸	good	🗸 Ø 336.637 µm 🖌	Ø 163,778.900 µm 🗸	Ø 208,465.200 µm 🗸	Ø 0.002 µm 🗸	Ø 0.020 µm 🗸	Ø 424.189 µm
217		Scan No. 11 [R=1 C=3] 🗸	good	🗸 Ø 339.363 µm 🖌	🖌 Ø 163,778.900 µm 🗸	Ø 176,465.200 µm 🗸	Ø 0.003 µm 🗸	Ø 0.032 µm 🖌	Ø 419.835 µm
4 4 4	Wafer Thickness [1] (12)	Scan No. 11 [R=2 C=2]	good	🗸 Ø 338.329 µm 🖌	🖉 Ø 155,778.900 µm 🖌	Ø 184,465.200 µm 🗸	Ø 0.012 µm 🖌	Ø 0.173 µm 🖌	Ø 422.175 µm
000	Scan No. 1 [R=2 C=4]	Scan No. 11 [R=2 C=3] 🗸	good	🖌 Ø 337.527 µm 🖌	🛿 Ø 163,778.900 µm 🔽	Ø 184,465.200 µm 🗸	Ø 0.004 µm 🖌	Ø 0.037 µm 🗹	Ø 425.367 µm
	Scan No. 1 [R=3 C=1]	Scan No. 11 [R=2 C=4] 🗸	good	🗸 Ø 336.598 µm 🖌	Ø 171,778.900 µm 🗸	Ø 184,465.200 µm 🗸	Ø 0.010 µm 🗸	Ø 0.095 µm 🗹	Ø 425.369 µm
111		Scan No. 11 [R=3 C=1] 🗸	good	🗸 Ø 335.948 µm 🖌	🖌 Ø 147,778.900 µm 🗸	Ø 192,465.200 µm 🗸	Ø 0.011 µm 🗸	Ø 0.104 µm 🖌	Ø 426.029 µm
	Thickness Mass rement ALR	Scan No. 11 [R=3 C=2] 🗸	good	🖌 Ø 336.796 µm 🖌	Ø 155,778.900 µm 🗸	Ø 192,465.200 µm 🗸	Ø 0.006 µm 🗸	Ø 0.055 µm 🗹	Ø 424.930 µm
111	Boughness [1] (26)	Scan No. 11 [R=3 C=3] 🗸	good	🗹 Ø 337.005 µm 🛛	Ø 163,778.900 µm 🖌	Ø 192,465.200 µm 🖌	Ø 0.003 µm 🔽	Ø 0.025 µm 🗹	Ø 424.924 µm
111		Scan No. 11 [R=3 C=4] 🗸	good	🗹 Ø 337.009 µm 🔤	🖉 Ø 171,778.900 µm 🔽	Ø 192,465.200 µm 🗸	Ø 0.010 µm 🗸	Ø 0.081 µm 🗹	Ø 424.809 µm
1 9		Scan No. 11 [R=3 C=5] 🗸	good	🗸 Ø 358.051 µm 🚽	🖉 Ø 179,778.900 µm 🗸	Ø 192,465.200 µm 🗸	Ø 0.007 µm 🗸	Ø 0.070 µm 🗸	Ø 381.944 µm
		Scan No. 11 [R=4 C=2]	good	🖌 Ø 336.692 µm 🔤	🖉 Ø 155,778.900 µm 🖌	Ø 200,465.200 µm 🗸	Ø 0.004 µm 🗸	Ø 0.031 µm 🗹	Ø 424.400 µm
		Scan No. 11 [R=4 C=3] 🖌	good	🖌 Ø 336.827 µm 🛛	🖉 Ø 163,778.900 µm 🖌	Ø 200,465.200 µm 🗸	Ø 0.002 µm 🗸	Ø 0.021 µm 🗹	Ø 424.193 µm
		Scan No. 11 [R=4 C=4] 🖌	good	🖌 Ø 337.423 µm 🚽	🖌 Ø 171,778.900 µm 🗸	Ø 200,465.200 µm 🗸	Ø 0.006 µm 🗸	Ø 0.044 µm 🖌	Ø 422.963 µm
H		Scan No. 11 [R=5 C=3] 🖌	good	🖌 Ø 336.670 µm 🚽	🖉 Ø 163,778.900 µm 🔽	Ø 208,465.200 µm 🖌	Ø 0.003 µm 🗸	Ø 0.025 µm 🗹	Ø 424.268 µm
111	Wafer Thickness [1] (32)	Scan No. 12 [R=1 C=3] 🗸	good	🖌 Ø 336.908 µm 🖌	🖉 Ø 163,778.900 µm 🖌	Ø 176,465.200 µm 🗸	Ø 0.003 µm 🗸	Ø 0.030 µm 🗹	Ø 424.908 µm
	Scan No. 1 [R=3 C=5]	Scan No. 12 [R=2 C=2]	good	🗹 Ø 338.657 µm 🛛	🖉 Ø 155,778.900 µm 🔽	Ø 184,465.200 µm 🔽	Ø 0.013 µm 🗸	Ø 0.184 µm 🗹	Ø 421.673 µm
	⊕** Scan No. 1 [R=4 C=2]	Scan No. 12 [R=2 C=3] 🗸	good	🗸 Ø 337.546 µm 🖌	Ø 163,778.900 µm 🗸	Ø 184,465.200 µm 🗸	Ø 0.003 µm 🗸	Ø 0.033 µm 🗹	Ø 425.427 µm
	B-1 Scan No. 1 [R=4 C=3]	Scan No. 12 [R=2 C=4] 🗸	good	🗸 Ø 338.390 µm 🖌	🖉 Ø 171,778.900 µm 🗸	Ø 184,465.200 µm 🗸	Ø 0.010 µm 🗸	Ø 0.093 µm 🖌	Ø 422.011 µm
		Scan No. 12 [R=3 C=1] 🗸	good	🗹 Ø 336.519 µm 📃	🖉 Ø 147,778.900 µm 🖌	Ø 192,465.200 µm 🗸	Ø 0.011 µm 🗸	Ø 0.108 µm 🗹	Ø 424.992 µm
1 Y 1	Scan No. 1 [K=5 C=3]	Scan No. 12 [R=3 C=2] 🗸	good	🖌 Ø 336.845 µm 🖌	Ø 155,778.900 µm 🖌	Ø 192,465.200 µm 🖌	Ø 0.007 µm 🗹	Ø 0.058 µm 🗹	Ø 424.962 µm
111	5can No. 2 [R=1 C=3]	Scan No. 12 [R=3 C=3] 🗸	good	🖌 Ø 337.055 µm 🚽	Ø 163,778.900 µm 🗸	Ø 192,465.200 µm 🖌	Ø 0.003 µm 🖌	Ø 0.023 µm 🗹	Ø 425.020 µm
111	< >	Scan No. 12 [R=3 C=4] 🗸	good	🖌 Ø 337.046 µm 🚽	Ø 171,778.900 µm 🖌	Ø 192,465.200 µm 🖌	Ø 0.010 µm 🖌	Ø 0.080 µm 🗹	Ø 424.927 µm
	Favorites Program Explorer	Scan No. 12 [R=3 C=5]	good	🗹 Ø 368.784 µm 🛛	Ø 179,778.900 µm 🔽	Ø 192,465.200 µm 🔽	Ø 0.007 µm 📝	Ø 0.073 µm 🗹	Ø 360.727 µm
· · · ·		Scan No. 12 [R=4 C=2]	qood	🗸 Ø 336.543 µm 🖌	🖉 Ø 155,778.900 µm 🗸	Ø 200,465.200 µm 🗸	Ø 0.004 µm 🗸	Ø 0.031 µm 🔽	Ø 424.874 µm

Stress Measurement

Flatness & Stress Measurement Gravity Compensation

Without Compensation

With Compensation

Stress Measurement

Gravity Compensation

Stress Measurement

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Q & A Session

Thank you.

Application Examples

- Full 2D/3D scans across small or large areas at predetermined locations
- Full 3D area measurements over the entire sample area
- Fully automatic determination of:
 - Height
 - Depth
 - Location
 - Flatness
 - Warpage
 - Roughness
 - Film Thickness
 - Thin Film Thickness
 - Bump Height, Vias, Diameter, Volume
 - Rotation vs custom reference/datum

- Tilt, Angle
- Distance, Width
- Bump Height, Vias, Diameter, Volume
- Coplanarity (Seating & Regression plane)
- Defects (as in missing features, spikes, scratches, bridges, indentations etc...)
- Bar-Code depth, roughness
- Edge chipping, edge quality, distance

CONFOCAL WHITE LIGHT SENSOR

	Single C- CHR sensor	Single P-CHR sensor	Dual P-CHR sensors	L-CHR Line Sensor
Profiles	1	1	1	192
Sampling Rate	4 kHz	4kHz -66 kHz	4kHz -66 kHz	up to 6 kHz
Data Points/s	4,000	up to 66,000	up to 66,000	up to 1,152,000
3D Scans	Raster	Raster	Raster	Single Scan 3D

LINE SENSOR – CONFOCAL WHITE LIGHT

Sensor	L-CHR-200	L-CHR-500	L-CHR-1000	L-CHR-2300	L-CHR-4000
Measurement Range (vertical)	200 µm	500 µm	950 µm	2300 µm	3900 µm
Line Length	0.96 mm	1.43 mm	1.91 mm	1.53 mm	4.78 mm
Pitch	5 µm	7.5 µm	10 µm	8 µm	25 µm
Working distance (WD)	5.3 mm	12mm	18.5 mm	15.6 mm	36.4 mm
Individual spot diameter	2 µm	3 µm	4 µm	3.2 µm	10 µm
Lateral resolution	1 µm	1.5 µm	2 µm	1.6 µm	5 µm
Axial (vertical) resolution	20 nm	50 nm	80 nm	200 nm	320 nm
NA	0.7	0.61	0.55	0.55	0.33
Angle to surface	90 +/- 44	90 +/- 38	90 +/- 33	90 +/- 33	90 +/- 20
Transparent Thickness measurement range	20 µm – 280 µm	40 μm – 700 μm	75 µm – 1.35 mm	200 µm – 3.1 mm	300 μm – 5.5 mm
Characterization	Very high resolution, steeper side-wall, short range	Sufficient range for many typical topographies, steep sidewall	Versatile all-around sensor with large WD	Large mst range, relatively high lateral resolution	Large mst range, narrow NA
Applications	Roughness, laser mark, micro- bumps, vias, pillars	Roughness, wire bond, laser mark, bumps, Cu pillars, RF antennae	Bumps, warpage, waviness, prints, vias	Surface shape, injection molded precision parts, channel depth	Mechanical components, larger topographies, shapes

CONFOCAL WHITE LIGHT SENSOR

